

ABSTRACT OF THE DISCLOSURE

A bipolar transistor device with a large current capacity is formed by connecting a plurality of transistor elements to each other in parallel, each transistor element having a collector layer, a base layer, and an emitter layer formed respectively in a semiconductor substrate. In the bipolar transistor device, the base layers of a plurality of the transistor elements are extended in parallel to each other and those base layers are separated from each other. In each separated base layer, a first base electrode is formed on a part of the base layer which is separated from an emitter junction with the emitter layer, and a second base electrode is formed on another portion of the base layer closer to the emitter junction than the first base electrode. To dispose the base electrodes of a plurality of the transistor elements in parallel to each other, a base wiring is connected to the first base electrodes of those elements electrically. Consequently, a ballast resistor that causes no variation in the resistance value can be connected to each of a plurality of the transistor elements.